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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	52
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l496rgt3

  - 2 x operational amplifiers with built-in PGA
  - 2 x ultra-low-power comparators
- 20 x communication interfaces
  - USB OTG 2.0 full-speed, LPM and BCD
  - 2 x SAIs (serial audio interface)
  - 4 x I2C FM+(1 Mbit/s), SMBus/PMBus
  - 5 x U(S)ARTs (ISO 7816, LIN, IrDA, modem)
  - 1 x LPUART
  - 3 x SPIs (4 x SPIs with the Quad SPI)
  - 2x CAN (2.0B Active) and SDMMC
  - SWPMI single wire protocol master I/F
  - IRTIM (Infrared interface)
- 14-channel DMA controller
- True random number generator
- CRC calculation unit, 96-bit unique ID
- Development support: serial wire debug (SWD), JTAG, Embedded Trace Macrocell™

Table 1. Device summary

Reference	Part numbers
STM32L496xx	STM32L496AG, STM32L496QG, STM32L496RG, STM32L496VG, STM32L496ZG, STM32L496AE, STM32L496QE, STM32L496RE, STM32L496VE, STM32L496ZE

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The Firewall main features are the following:

- Three segments can be protected and defined thanks to the Firewall registers:
  - Code segment (located in Flash or SRAM1 if defined as executable protected area)
  - Non-volatile data segment (located in Flash)
  - Volatile data segment (located in SRAM1)
- The start address and the length of each segments are configurable:
  - code segment: up to 1024 Kbyte with granularity of 256 bytes
  - Non-volatile data segment: up to 1024 Kbyte with granularity of 256 bytes
  - Volatile data segment: up to 256 Kbyte of SRAM1 with a granularity of 64 bytes
- Specific mechanism implemented to open the Firewall to get access to the protected areas (call gate entry sequence)
- Volatile data segment can be shared or not with the non-protected code
- Volatile data segment can be executed or not depending on the Firewall configuration

The Flash readout protection must be set to level 2 in order to reach the expected level of protection.

3.8 Boot modes

At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

BOOT0 value may come from the PH3-BOOT0 pin or from an option bit depending on the value of a user option bit to free the GPIO pad if needed.

A Flash empty check mechanism is implemented to force the boot from system flash if the first flash memory location is not programmed and if the boot selection is configured to boot from main flash.

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART, I2C, SPI, CAN and USB OTG FS in Device mode through DFU (device firmware upgrade).

3.9 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.10.3 Voltage regulator

Two embedded linear voltage regulators supply most of the digital circuitries: the main regulator (MR) and the low-power regulator (LPR).

- The MR is used in the Run and Sleep modes and in the Stop 0 mode.
- The LPR is used in Low-Power Run, Low-Power Sleep, Stop 1 and Stop 2 modes. It is also used to supply the 64 Kbyte SRAM2 in Standby with RAM2 retention.
- Both regulators are in power-down in Standby and Shutdown modes: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

The ultralow-power STM32L496xx supports dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the Main Regulator that supplies the logic (VCORE) can be adjusted according to the system's maximum operating frequency.

There are two power consumption ranges:

- Range 1 with the CPU running at up to 80 MHz.
- Range 2 with a maximum CPU frequency of 26 MHz. All peripheral clocks are also limited to 26 MHz.

The VCORE can be supplied by the low-power regulator, the main regulator being switched off. The system is then in Low-power run mode.

- Low-power run mode with the CPU running at up to 2 MHz. Peripherals with independent clock can be clocked by HSI16.

When the MR is in use, the STM32L496xx with the external SMPS option allows to force an external VCORE supply on the VDD12 supply pins.

When VDD12 is forced by an external source and is higher than the output of the internal LDO, the current is taken from this external supply and the overall power efficiency is significantly improved if using an external step down DC/DC converter.

3.10.4 Low-power modes

The ultra-low-power STM32L496xx supports seven low-power modes to achieve the best compromise between low-power consumption, short startup time, available peripherals and available wakeup sources:

Table 4. STM32L496xx modes overview

Mode	Regulator[1]	CPU	Flash	SRAM	Clocks	DMA & Peripherals[2]	Wakeup source	Consumption[3]	Wakeup time
Run	MR range 1	Yes	ON[4]	ON	Any	All	N/A	108 µA/MHz	N/A
	SMPS range 2 High							40 µA/MHz[5]	
	MR range2					All except OTG_FS, RNG		93 µA/MHz	
	SMPS range 2 Low							39 µA/MHz[6]	
LPRun	LPR	Yes	ON[4]	ON	Any except PLL	All except OTG_FS, RNG	N/A	129 µA/MHz	to Range 1: 4 µs to Range 2: 64 µs
Sleep	MR range 1	No	ON[4]	ON[7]	Any	All	Any interrupt or event	32 µA/MHz	6 cycles
	SMPS range 2 High							11.5 µA/MHz[5]	
	MR range2					All except OTG_FS, RNG		30 µA/MHz	
	SMPS range 2 Low							13 µA/MHz[6]	
LPSleep	LPR	No	ON[4]	ON[7]	Any except PLL	All except OTG_FS, RNG	Any interrupt or event	51 µA/MHz	6 cycles
Stop 0	MR Range 1[8]	No	OFF	ON	LSE LSI	BOR, PVD, PVM RTC,LCD, IWDG COMPx (x=1,2) DACx (x=1,2) OPAMPx (x=1,2) USARTx (x=1...5)[9] LPUART1[9] I2Cx (x=1...4)[10] LPTIMx (x=1,2) *** All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=1..2) USARTx (x=1...5)[9] LPUART1[9] I2Cx (x=1...34)[10] LPTIMx (x=1,2) OTG_FS[11] SWPMI1[12]	TBD	2.7 µs in SRAM 6.2 µs in Flash
	MR Range 2[8]							127 µA	

3.28 Real-time clock (RTC) and backup registers

The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Two programmable alarms.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 0.95 ppm resolution, to compensate for quartz crystal inaccuracy.
- Three anti-tamper detection pins with programmable filter.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event, or by a switch to VBAT mode.
- 17-bit auto-reload wakeup timer (WUT) for periodic events with programmable resolution and period.

The RTC and the 32 backup registers are supplied through a switch that takes power either from the V_{DD} supply when present or from the VBAT pin.

The backup registers are 32-bit registers used to store 128 bytes of user application data when VDD power is not present. They are not reset by a system or power reset, or when the device wakes up from Standby or Shutdown mode.

The RTC clock sources can be:

- A 32.768 kHz external crystal (LSE)
- An external resonator or oscillator (LSE)
- The internal low power RC oscillator (LSI, with typical frequency of 32 kHz)
- The high-speed external clock (HSE) divided by 32.

The RTC is functional in VBAT mode and in all low-power modes when it is clocked by the LSE. When clocked by the LSI, the RTC is not functional in VBAT mode, but is functional in all low-power modes except Shutdown mode.

All RTC events (Alarm, WakeUp Timer, Timestamp or Tamper) can generate an interrupt and wakeup the device from the low-power modes.

Dual CAN peripheral configuration is available. The CAN peripheral supports:

- Supports CAN protocol version 2.0 A, B Active
- Bit rates up to 1 Mbit/s
- Transmission
  - Three transmit mailboxes
  - Configurable transmit priority
- Reception
  - Two receive FIFOs with three stages
  - Scalable filter banks: 28 filter banks shared between CAN1 and CAN2
  - Identifier list feature
  - Configurable FIFO overrun
- Time-triggered communication option
  - Disable automatic retransmission mode
  - 16-bit free running timer
  - Time Stamp sent in last two data bytes
- Management
  - Maskable interrupts
  - Software-efficient mailbox mapping at a unique address space

3.36 Secure digital input/output and MultiMediaCards Interface (SDMMC)

The card host interface (SDMMC) provides an interface between the APB peripheral bus and MultiMediaCards (MMCs), SD memory cards and SDIO cards.

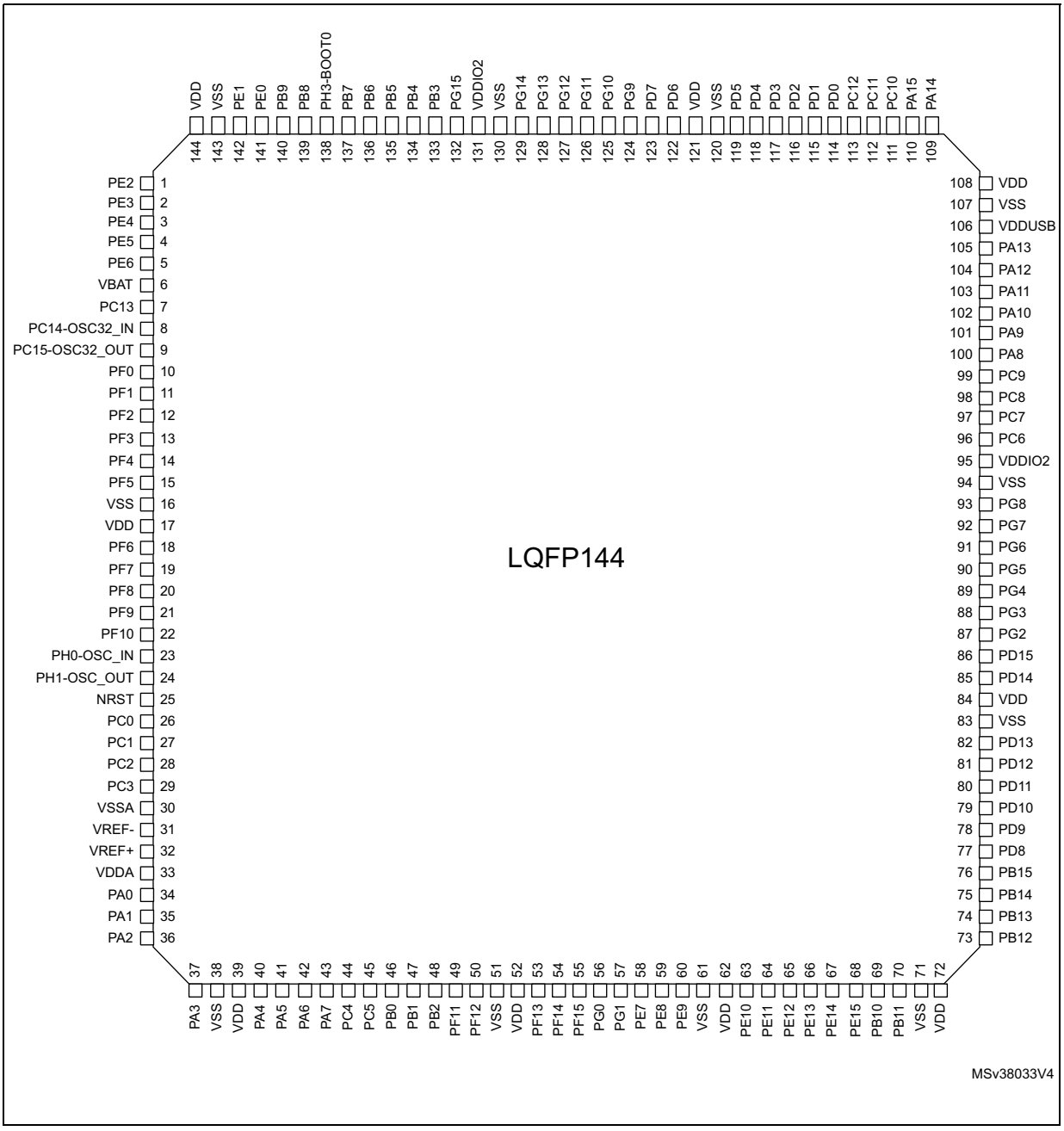
The SDMMC features include the following:

- Full compliance with MultiMediaCard System Specification Version 4.2. Card support for three different databus modes: 1-bit (default), 4-bit and 8-bit
- Full compatibility with previous versions of MultiMediaCards (forward compatibility)
- Full compliance with SD Memory Card Specifications Version 2.0
- Full compliance with SD I/O Card Specification Version 2.0: card support for two different databus modes: 1-bit (default) and 4-bit
- Data transfer up to 48 MHz for the 8 bit mode
- Data write and read with DMA capability

3.37 Universal serial bus on-the-go full-speed (OTG_FS)

The devices embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that can be provided by the internal multispeed oscillator (MSI) automatically trimmed by 32.768 kHz external oscillator (LSE).This allows to use the USB device without external high speed crystal (HSE).

Figure 8. STM32L496Zx LQFP144 pinout(1)



1. The above figure shows the package top view.

Table 15. STM32L496xx pin definitions (continued)

Pin Number									Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP100	WLCSP100_SMPS	LQFP100	UFBGA132	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS					Alternate functions	Additional functions
61	B8	B8	95	A3	139	138	C4	C4	PB8	I/O	FT_fl	-	TIM4_CH3, I2C1_SCL, DFSDM1_DATIN6, CAN1_RX, DCMI_D6, LCD_SEG16, SDMMC1_D4, SAI1_MCLK_A, TIM16_CH1, EVENTOUT	-
62	A8	A8	96	B3	140	139	D4	D4	PB9	I/O	FT_fl	-	IR_OUT, TIM4_CH4, I2C1_SDA, SPI2_NSS, DFSDM1_CKIN6, CAN1_TX, DCMI_D7, LCD_COM3, SDMMC1_D5, SAI1_FS_A, TIM17_CH1, EVENTOUT	-
-	-	-	-	-	-	-	-	C6	VDD12	S	-	-	-	-
-	-	-	97	C3	141	140	A4	A4	PE0	I/O	FT_l	-	TIM4_ETR, DCMI_D2, LCD_SEG36, FMC_NBL0, TIM16_CH1, EVENTOUT	-
-	-	-	98	A2	142	141	B4	B4	PE1	I/O	FT_l	-	DCMI_D3, LCD_SEG37, FMC_NBL1, TIM17_CH1, EVENTOUT	-
-	-	A9	-	-	-	142	-	-	VDD12	S	-	-	-	-
63	A9	B9	99	D3	143	143	B3	B3	VSS	S	-	-	-	-
64	A10	A10	100	C4	144	144	A3	A3	VDD	S	-	-	-	-
-	-	-	-	-	-	-	C2	C2	VSS	S	-	-	-	-
-	-	-	-	-	-	-	C1	C1	VDD	S	-	-	-	-
-	-	-	-	-	-	-	A2	A2	PH2	I/O	FT	-	QUADSPI_BK2_IO0, EVENTOUT	-

1. OPAMPx_VINM pins are not available as additional functions on pins PA1 and PA7 on UFBGA packages. On UFBGA packages, use the OPAMPx_VINM dedicated pins available on M3 and M4 balls.

Table 18. STM32L496xx memory map and peripheral register boundary addresses(1) (continued)

Bus	Boundary address	Size (bytes)	Peripheral
APB1	0x4000 4800 - 0x4000 4BFF	1 KB	USART3
	0x4000 4400 - 0x4000 47FF	1 KB	USART2
	0x4000 4000 - 0x4000 43FF	1 KB	Reserved
	0x4000 3C00 - 0x4000 3FFF	1 KB	SPI3
	0x4000 3800 - 0x4000 3BFF	1 KB	SPI2
	0x4000 3400 - 0x4000 37FF	1 KB	Reserved
	0x4000 3000 - 0x4000 33FF	1 KB	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 KB	WWDG
	0x4000 2800 - 0x4000 2BFF	1 KB	RTC
	0x4000 2400 - 0x4000 27FF	1 KB	LCD
	0x4000 1800 - 0x4000 23FF	3 KB	Reserved
	0x4000 1400 - 0x4000 17FF	1 KB	TIM7
	0x4000 1000 - 0x4000 13FF	1 KB	TIM6
	0x4000 0C00- 0x4000 0FFF	1 KB	TIM5
	0x4000 0800 - 0x4000 0BFF	1 KB	TIM4
	0x4000 0400 - 0x4000 07FF	1 KB	TIM3
	0x4000 0000 - 0x4000 03FF	1 KB	TIM2

1. The gray color is used for reserved boundary addresses.

6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 23* are derived from tests performed under the ambient temperature condition summarized in *Table 22*.

Table 23. Operating conditions at power-up / power-down(1)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	µs/V
	V_{DD} fall time rate		10	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	µs/V
	V_{DDA} fall time rate		10	∞	
t_{VDDUSB}	V_{DDUSB} rise time rate	-	0	∞	µs/V
	V_{DDUSB} fall time rate		10	∞	
t_{VDDIO2}	V_{DDIO2} rise time rate	-	0	∞	µs/V
	V_{DDIO2} fall time rate		10	∞	

1. At Power up, the VDD12 voltage should not be forced externally

6.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 24* are derived from tests performed under the ambient temperature conditions summarized in *Table 22: General operating conditions*.

Table 24. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions(1)	Min	Typ	Max	Unit
$t_{RSTTEMPO}$(2)	Reset temporization after BOR0 is detected	V_{DD} rising	-	250	400	µs
V_{BOR0}(2)	Brown-out reset threshold 0	Rising edge	1.62	1.66	1.7	V
		Falling edge	1.6	1.64	1.69	
V_{BOR1}	Brown-out reset threshold 1	Rising edge	2.06	2.1	2.14	V
		Falling edge	1.96	2	2.04	
V_{BOR2}	Brown-out reset threshold 2	Rising edge	2.26	2.31	2.35	V
		Falling edge	2.16	2.20	2.24	
V_{BOR3}	Brown-out reset threshold 3	Rising edge	2.56	2.61	2.66	V
		Falling edge	2.47	2.52	2.57	
V_{BOR4}	Brown-out reset threshold 4	Rising edge	2.85	2.90	2.95	V
		Falling edge	2.76	2.81	2.86	
V_{PVD0}	Programmable voltage detector threshold 0	Rising edge	2.1	2.15	2.19	V
		Falling edge	2	2.05	2.1	
V_{PVD1}	PVD threshold 1	Rising edge	2.26	2.31	2.36	V
		Falling edge	2.15	2.20	2.25	

Table 24. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions[1]	Min	Typ	Max	Unit
V_{PVD2}	PVD threshold 2	Rising edge	2.41	2.46	2.51	V
		Falling edge	2.31	2.36	2.41	
V_{PVD3}	PVD threshold 3	Rising edge	2.56	2.61	2.66	V
		Falling edge	2.47	2.52	2.57	
V_{PVD4}	PVD threshold 4	Rising edge	2.69	2.74	2.79	V
		Falling edge	2.59	2.64	2.69	
V_{PVD5}	PVD threshold 5	Rising edge	2.85	2.91	2.96	V
		Falling edge	2.75	2.81	2.86	
V_{PVD6}	PVD threshold 6	Rising edge	2.92	2.98	3.04	V
		Falling edge	2.84	2.90	2.96	
V_{hyst_BORH0}	Hysteresis voltage of BORH0	Hysteresis in continuous mode	-	20	-	mV
		Hysteresis in other mode	-	30	-	
$V_{hyst\_BOR\_PVD}$	Hysteresis voltage of BORH (except BORH0) and PVD	-	-	100	-	mV
I_{DD} (BOR_PVD)[2]	BOR[3] (except BOR0) and PVD consumption from V_{DD}	-	-	1.1	1.6	µA
V_{PVM3}	V_{DDA} peripheral voltage monitoring	Rising edge	1.61	1.65	1.69	V
		Falling edge	1.6	1.64	1.68	
V_{PVM4}	V_{DDA} peripheral voltage monitoring	Rising edge	1.78	1.82	1.86	V
		Falling edge	1.77	1.81	1.85	
V_{hyst_PVM3}	PVM3 hysteresis	-	-	10	-	mV
V_{hyst_PVM4}	PVM4 hysteresis	-	-	10	-	mV
I_{DD} (PVM1/PVM2) (2)	PVM1 and PVM2 consumption from V_{DD}	-	-	0.2	-	µA
I_{DD} (PVM3/PVM4) (2)	PVM3 and PVM4 consumption from V_{DD}	-	-	2	-	µA

1. Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.
2. Guaranteed by design.
3. BOR0 is enabled in all modes (except shutdown) and its consumption is therefore included in the supply current characteristics tables.

Table 43. Current consumption in Low-power sleep modes, Flash in power-down

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	92.7	124	258	487	968	105	224	474	969	2006	µA
				1 MHz	63.5	97.5	223	460	951	75	193	446	942	1975	
				400 kHz	42.6	75.6	207	443	947	54	171	426	923	1955	
				100 kHz	31.2	67.6	199	437	905	44	162	420	916	1947	

1. Guaranteed by characterization results, unless otherwise specified.

Table 44. Current consumption in Stop 2 mode

Symbol	Parameter	Conditions		TYP					MAX(1)					Unit
		-	V_{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (Stop 2)	Supply current in Stop 2 mode, RTC disabled	LCD disabled	1.8 V	2.57	6.86	25.2	60.1	135	5.3	16.4	64	154.6	353	µA
			2.4 V	2.62	6.91	25.5	60.6	137	5.3	16.6	64.9	156.7	359	
			3 V	2.69	6.93	25.7	61.5	140	5.4	16.9	66.3	159.7	366	
			3.6 V	2.7	7.08	26.3	62.9	143	5.4	17.4	67.8	163.8	375	
		LCD enabled(2) clocked by LSI	1.8 V	2.92	7.19	25.3	59.5	135	5.3	16.6	64.8	155.6	355	
			2.4 V	2.99	7.3	25.6	60.3	136	5.5	16.8	65.9	157.9	360	
			3 V	3.04	7.41	26.1	61.7	140	5.9	17.3	67.1	160.8	367	
			3.6 V	3.31	7.7	26.8	63.2	143	6.2	17.9	69.1	165.0	376	

Table 59. MSI oscillator characteristics(1) (continued)

Symbol	Parameter	Conditions			Min	Typ	Max	Unit
$\Delta_{VDD}(MSI)^{(2)}$	MSI oscillator frequency drift over V_{DD} (reference is 3 V)	MSI mode	Range 0 to 3	V_{DD}=1.62 V to 3.6 V	-1.2	-	0.5	%
				V_{DD}=2.4 V to 3.6 V	-0.5	-		
			Range 4 to 7	V_{DD}=1.62 V to 3.6 V	-2.5	-	0.7	
				V_{DD}=2.4 V to 3.6 V	-0.8	-		
			Range 8 to 11	V_{DD}=1.62 V to 3.6 V	-5	-	1	
				V_{DD}=2.4 V to 3.6 V	-1.6	-		
$\Delta F_{SAMPLING}(MSI)^{(2)(4)}$	Frequency variation in sampling mode(3)	MSI mode	T_A= -40 to 85 °C		-	1	2	%
			T_A= -40 to 125 °C		-	2	4	
CC jitter(MSI)(4)	RMS cycle-to-cycle jitter	PLL mode Range 11		-	-	60	-	ps
P jitter(MSI)(4)	RMS Period jitter	PLL mode Range 11		-	-	50	-	ps
$t_{SU}(MSI)^{(4)}$	MSI oscillator start-up time	Range 0		-	-	10	20	us
		Range 1		-	-	5	10	
		Range 2		-	-	4	8	
		Range 3		-	-	3	7	
		Range 4 to 7		-	-	3	6	
		Range 8 to 11		-	-	2.5	6	
$t_{STAB}(MSI)^{(4)}$	MSI oscillator stabilization time	PLL mode Range 11	10 % of final frequency	-	-	0.25	0.5	ms
			5 % of final frequency	-	-	0.5	1.25	
			1 % of final frequency	-	-	-	2.5	

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 68. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A(1)

1. Negative injection is limited to -30 mA for PF0, PF1, PG6, PG7, PG8, PG12, PG13, PG14.

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DDIOx} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the -5 µA/+0 µA range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in *Table 69*.

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Table 69. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}(1)	Injected current on all pins except PA4, PA5, PB0, PF12, PF13, OPAMP1_V1NM, OPAMP2_V1NM	-5	NA	mA
	Injected current on pins PB0, PF12, PF13	0	NA	
	Injected current on OPAMP1_V1NM, OPAMP2_V1NM	0	0	
	Injected current on PA4, PA5 pins	-5	0	

1. Guaranteed by characterization.

Table 72. I/O AC characteristics(1)(2)

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
00	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	5	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	10	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1.5	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	52	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	140	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	17	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	37	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	110	
01	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	10	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	50	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	15	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	9	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	16	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	40	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	4.5	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	9	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	21	

Figure 37. Quad SPI timing diagram - SDR mode

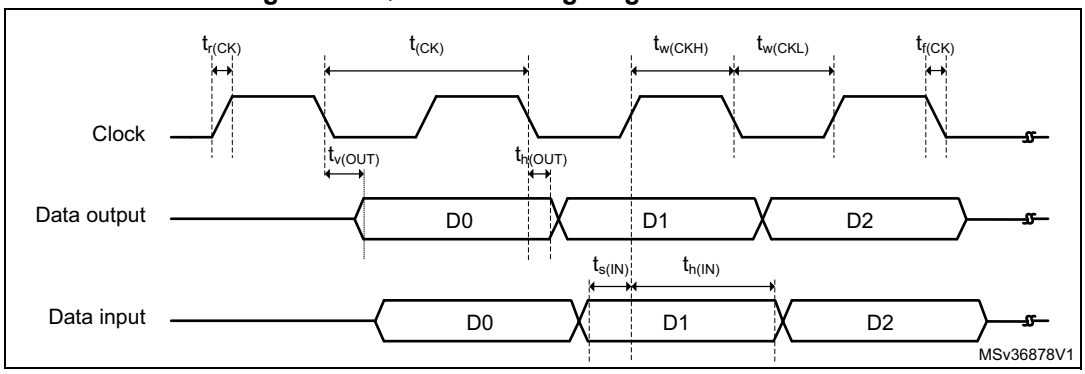


Figure 38. Quad SPI timing diagram - DDR mode

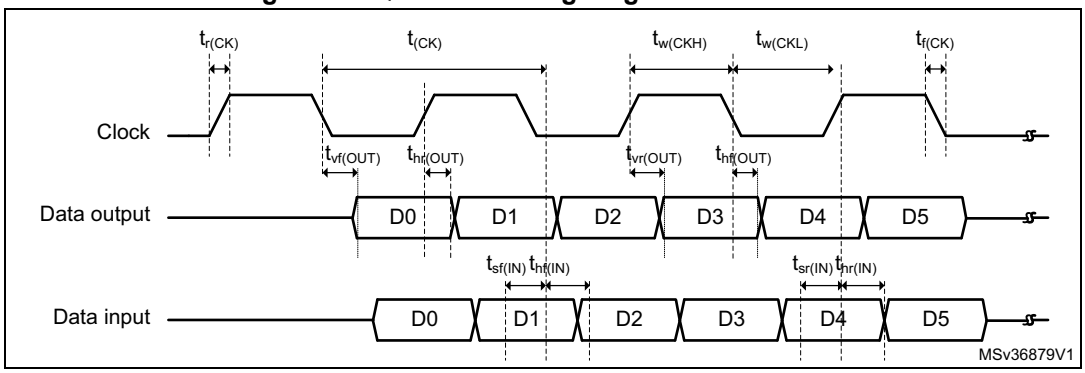


Figure 44. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms

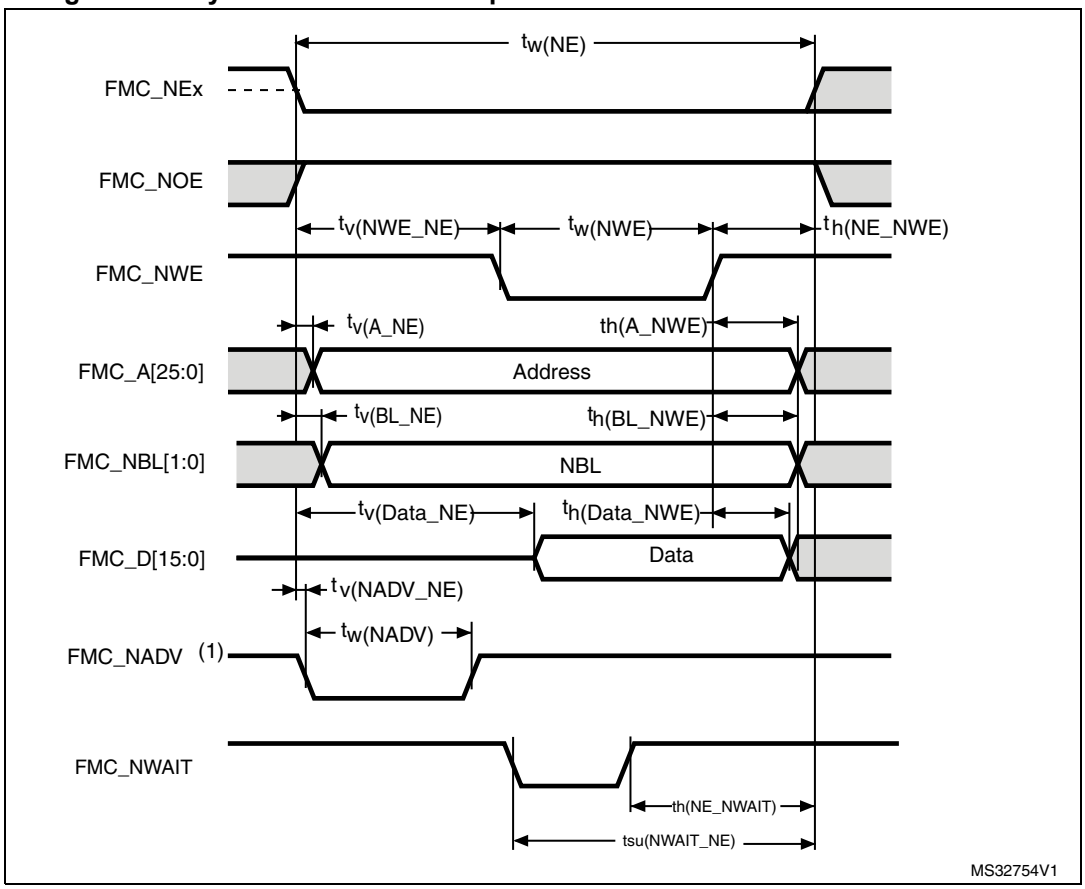


Table 104. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}$-1	$3T_{HCLK}$+1	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	T_{HCLK}-1	T_{HCLK}+1	
$t_{w(NWE)}$	FMC_NWE low time	T_{HCLK}-1.5	T_{HCLK}+ 0.5	
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	T_{HCLK}	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0	
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	T_{HCLK}-0.5	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0.5	
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	T_{HCLK}-0.5	-	
$t_{v(Data\_NE)}$	Data to FMC_NEx low to Data valid	-	T_{HCLK}+3	
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	T_{HCLK}+0.5	-	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	-	0	
$t_{w(NADV)}$	FMC_NADV low time	-	T_{HCLK}+1	

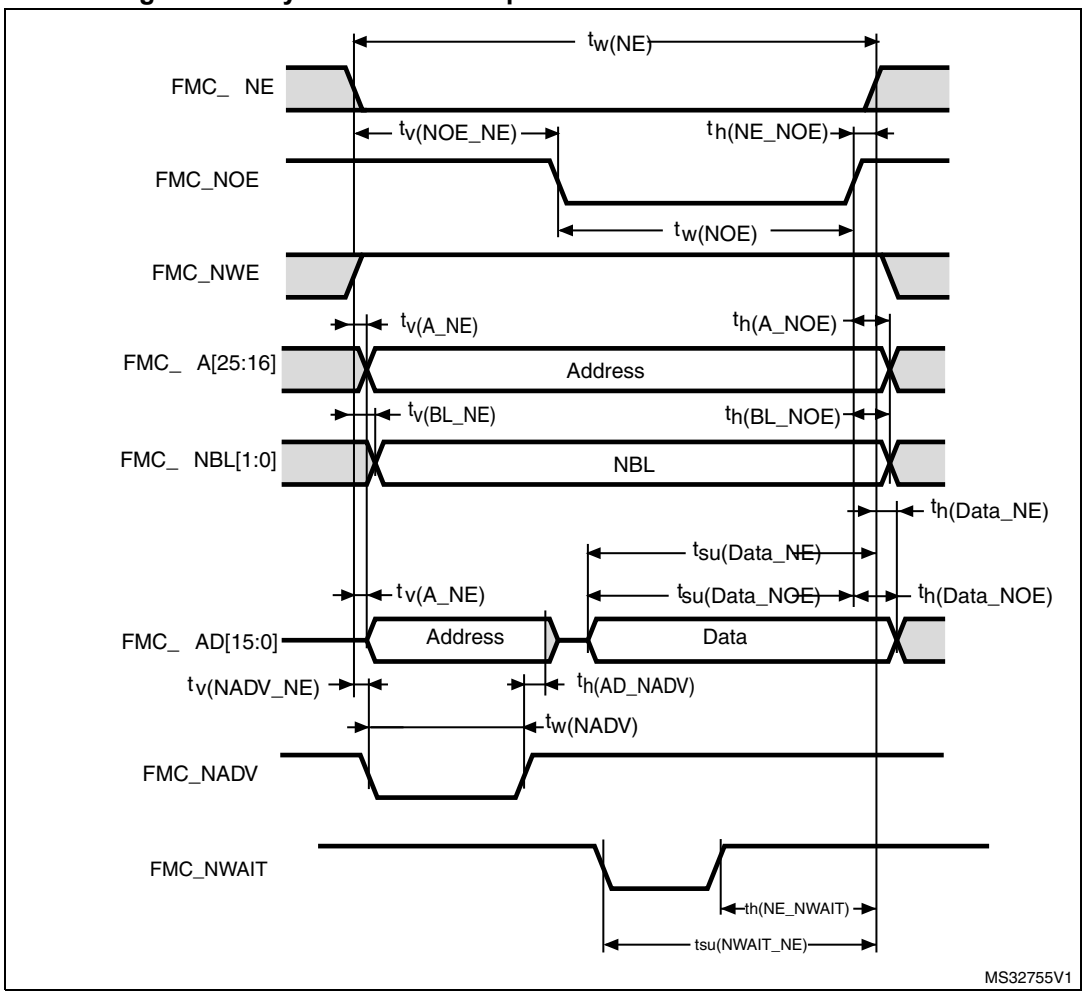
1. CL = 30 pF.
2. Guaranteed by characterization results.

Table 105. Asynchronous non-multiplexed SRAM/PSRAM/NOR write-NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}$-1	$8T_{HCLK}$+1	ns
$t_{w(NWE)}$	FMC_NWE low time	$6T_{HCLK}$-1.5	$6T_{HCLK}$+0.5	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK}$-1	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}$+2	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

Figure 45. Asynchronous multiplexed PSRAM/NOR read waveforms



9 Revision history

Table 131. Document revision history

Date	Revision	Changes
22-Feb-2017	1	Initial release.